Form PTO 1449		U.S. DEPARTMENT	OF COMMERCE	ATTY DOCKET NO. 245908US2S		SERIAL NO.		
(Modified)		PATENT AND TRAC	EMARK OFFICE			NEW APPLICATION		
				APPLICANT				
LIST OF REFERENCES CITED BY APPLICANT				Katsuhiko HOYA, et al.				
				FILING DATE		GROUP		
				HEREWITH				
			1	U.S. PATENT DOCUMENTS		<del> </del>		
EXAMINER		DOCUMENT	5475		CLASS	SUB	FILING DATE	
INITIAL		NUMBER	DATE	NAME	CLASS	CLASS	IF APPROPRIATE	
HU	AA	6,366,490 B1	04/02/02	Yoshiaki TAKEUCHI, et al.				
	AB							
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		OTHER RE	FERENCES (	Including Author, Title, Date, Pertinen	t Pages, e	tc.)		
IN	AW	D. TAKASHIMA, et al., "High-Density Chain Ferroelectric Random-Access Memory (CFRAM)", SYMPOSIUM ON VLSI CIRCUITS DIGEST OF TECHNICAL PAPERS, 1997, pgs. 83-84						
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					Add	itional Refe	erences sheet(s) attached	
Examiner	AY AZ	Ituan	itran	্র t citation is in conformance with MPEP 6	Date Co	nsidered	9/29/04	